

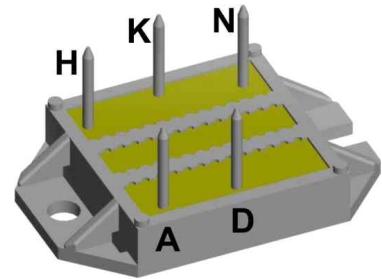
Standard Rectifier Module

3~ Rectifier	
V_{RRM}	= 1200 V
I_{DAV}	= 30 A
I_{FSM}	= 120 A

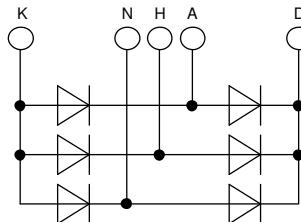
3~ Rectifier Bridge

Part number

VUO28-12NO7



 E72873



Features / Advantages:

- Package with DCB ceramic
- Improved temperature and power cycling
- Planar passivated chips
- Very low forward voltage drop
- Very low leakage current

Applications:

- Diode for main rectification
- For three phase bridge configurations
- Supplies for DC power equipment
- Input rectifiers for PWM inverter
- Battery DC power supplies
- Field supply for DC motors

Package: ECO-PAC1

- Isolation Voltage: 3000 V~
- Industry standard outline
- RoHS compliant
- Soldering pins for PCB mounting
- Height: 9 mm
- Base plate: DCB ceramic
- Reduced weight
- Advanced power cycling

Disclaimer Notice

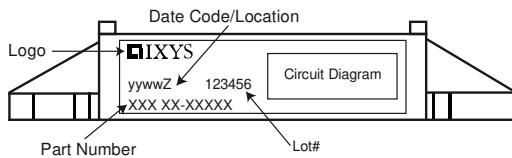
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Rectifier

Symbol	Definition	Conditions	Ratings			
			min.	typ.	max.	
V_{RSM}	max. non-repetitive reverse blocking voltage	$T_{VJ} = 25^\circ C$			1300	V
V_{RRM}	max. repetitive reverse blocking voltage	$T_{VJ} = 25^\circ C$			1200	V
I_R	reverse current	$V_R = 1200 \text{ V}$ $V_R = 1200 \text{ V}$	$T_{VJ} = 25^\circ C$ $T_{VJ} = 150^\circ C$		10 0.7	μA mA
V_F	forward voltage drop	$I_F = 10 \text{ A}$	$T_{VJ} = 25^\circ C$		1.20	V
		$I_F = 30 \text{ A}$			1.61	V
		$I_F = 10 \text{ A}$	$T_{VJ} = 125^\circ C$		1.14	V
		$I_F = 30 \text{ A}$			1.68	V
I_{DAV}	bridge output current	$T_C = 105^\circ C$ rectangular $d = 1/3$	$T_{VJ} = 150^\circ C$		30	A
V_{F0} r_F	threshold voltage slope resistance } for power loss calculation only		$T_{VJ} = 150^\circ C$		0.84	V
					28.8	$m\Omega$
R_{thJC}	thermal resistance junction to case				2.5	K/W
R_{thCH}	thermal resistance case to heatsink			0.4		K/W
P_{tot}	total power dissipation		$T_C = 25^\circ C$		50	W
I_{FSM}	max. forward surge current	$t = 10 \text{ ms}; (50 \text{ Hz}), \text{sine}$	$T_{VJ} = 45^\circ C$		120	A
		$t = 8,3 \text{ ms}; (60 \text{ Hz}), \text{sine}$	$V_R = 0 \text{ V}$		130	A
		$t = 10 \text{ ms}; (50 \text{ Hz}), \text{sine}$	$T_{VJ} = 150^\circ C$		100	A
		$t = 8,3 \text{ ms}; (60 \text{ Hz}), \text{sine}$	$V_R = 0 \text{ V}$		110	A
I^2t	value for fusing	$t = 10 \text{ ms}; (50 \text{ Hz}), \text{sine}$	$T_{VJ} = 45^\circ C$		72	A^2s
		$t = 8,3 \text{ ms}; (60 \text{ Hz}), \text{sine}$	$V_R = 0 \text{ V}$		70	A^2s
		$t = 10 \text{ ms}; (50 \text{ Hz}), \text{sine}$	$T_{VJ} = 150^\circ C$		50	A^2s
		$t = 8,3 \text{ ms}; (60 \text{ Hz}), \text{sine}$	$V_R = 0 \text{ V}$		50	A^2s
C_J	junction capacitance	$V_R = 400 \text{ V}; f = 1 \text{ MHz}$	$T_{VJ} = 25^\circ C$	4		pF

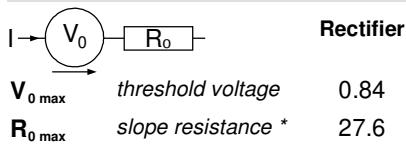
Package ECO-PAC1

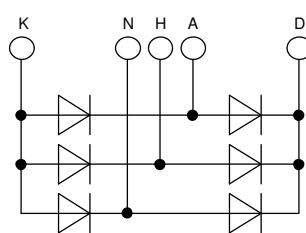
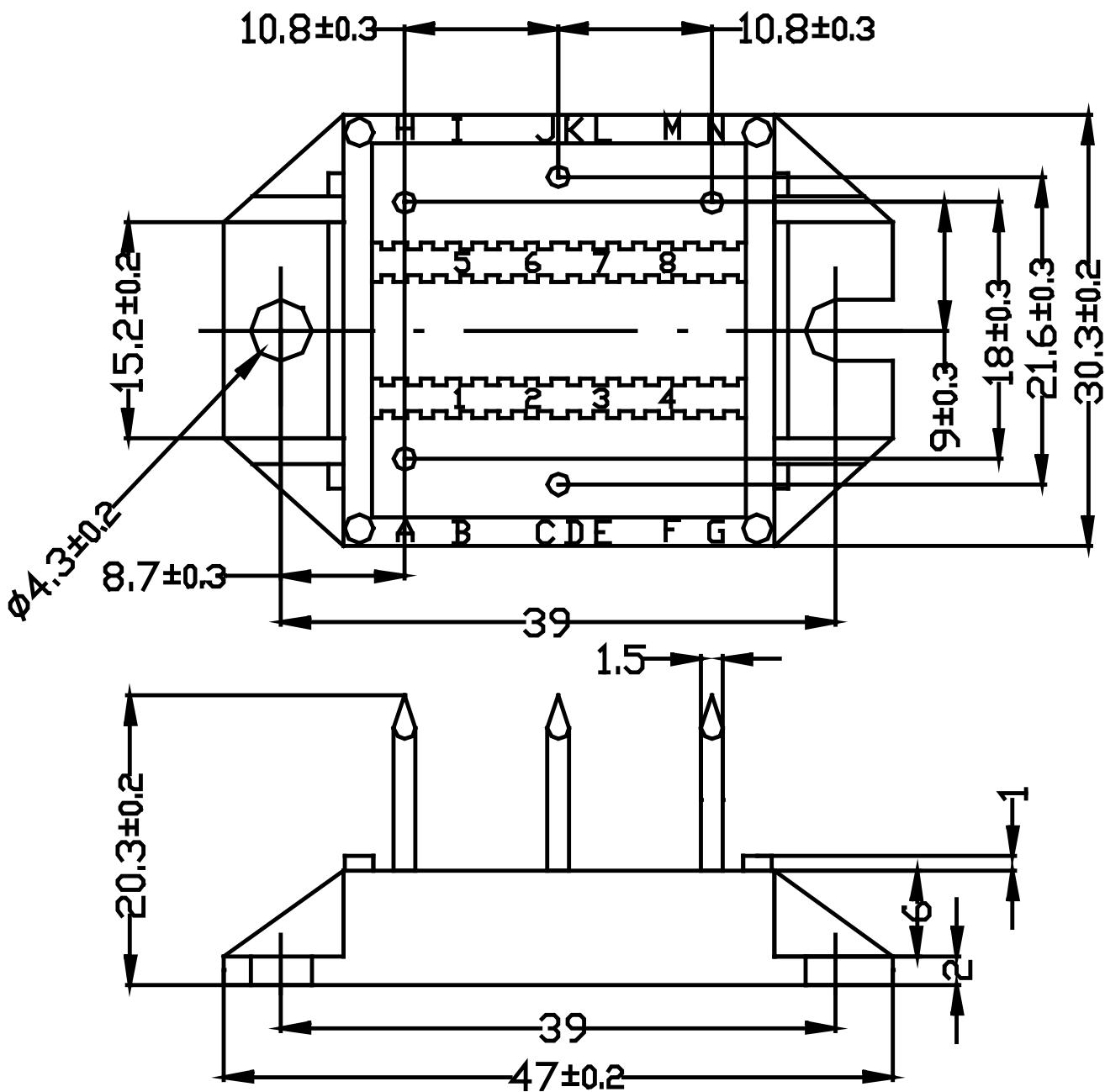
Symbol	Definition	Conditions	Ratings			
			min.	typ.	max.	
I_{RMS}	RMS current	per terminal			100	A
T_{VJ}	virtual junction temperature		-40		150	°C
T_{op}	operation temperature		-40		125	°C
T_{stg}	storage temperature		-40		125	°C
Weight				19		g
M_D	mounting torque		1.4		2	Nm
$d_{Spp/App}$	creepage distance on surface / striking distance through air	terminal to terminal	6.0			mm
$d_{Spb/Apb}$		terminal to backside	10.0			mm
V_{ISOL}	isolation voltage	t = 1 second t = 1 minute 50/60 Hz, RMS; $I_{ISOL} \leq 1$ mA	3000 2500			V



Ordering	Ordering Number	Marking on Product	Delivery Mode	Quantity	Code No.
Standard	VUO28-12NO7	VUO28-12NO7	Box	25	479632

Equivalent Circuits for Simulation
^{*}on die level

 $T_{VJ} = 150^\circ\text{C}$


Outlines ECO-PAC1


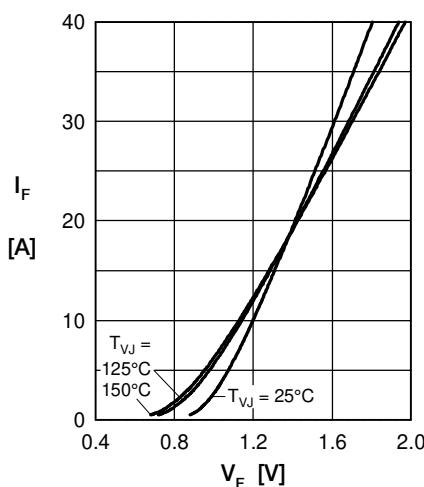
Rectifier


Fig. 1 Forward current vs.
voltage drop per diode

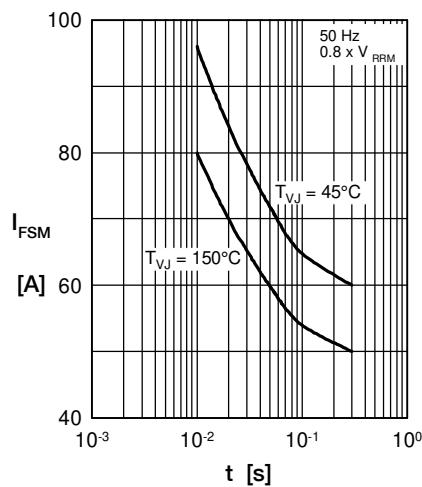


Fig. 2 Surge overload current
vs. time per diode

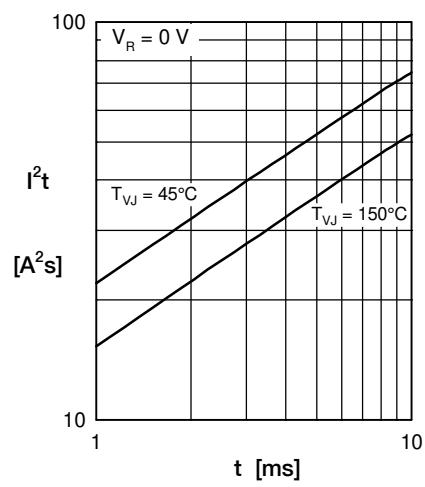


Fig. 3 I^2t vs. time per diode

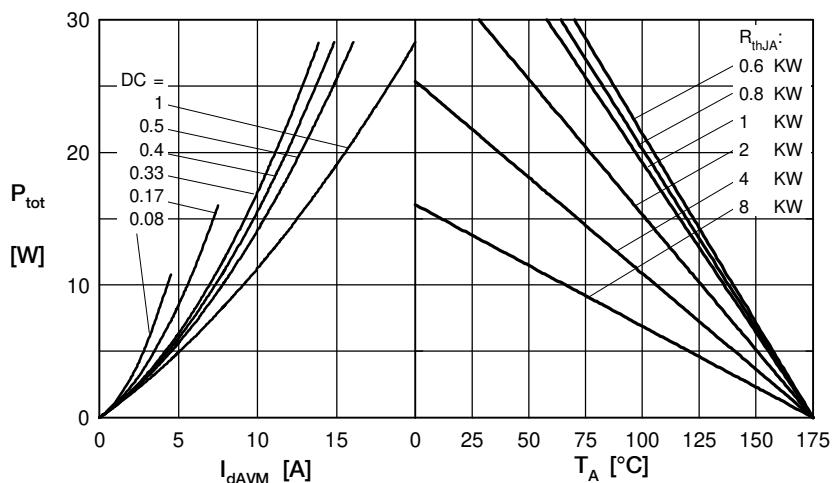


Fig. 4 Power dissipation vs. forward current
and ambient temperature per diode

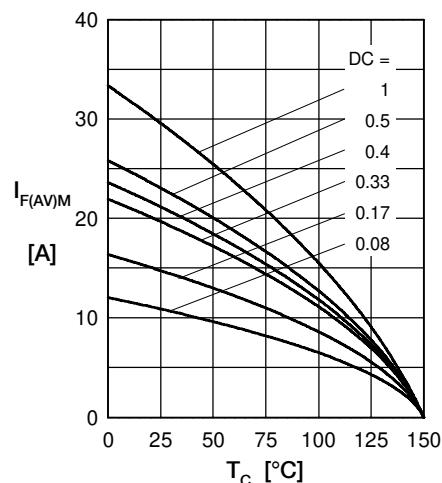


Fig. 5 Max. forward current vs.
case temperature per diode

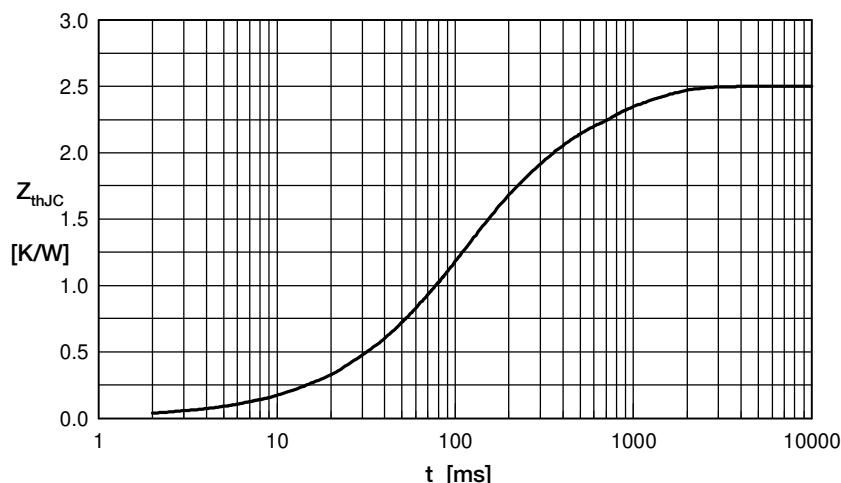


Fig. 6 Transient thermal impedance junction to case vs. time per diode

Constants for Z_{thJC} calculation:

i	R_{th} (K/W)	t_i (s)
1	1.359	0.1015
2	0.3286	0.1026
3	0.1651	0.4919
4	0.6473	0.62